

# Vishay High Power Products

# **HEXFRED® Ultrafast Soft Recovery Diode, 180 A**





Lug terminal anode

Base

PRODUCT SUMMARY					
I <sub>F(AV)</sub>	180 A				
$V_{R}$	400 V				
I <sub>E(DC)</sub> at T <sub>C</sub>	200 A at 100 °C				

#### **FEATURES**

- Very low Q<sub>rr</sub> and t<sub>rr</sub>
- · Lead (Pb)-free
- · Designed and qualified for industrial level



#### **BENEFITS**

- · Reduced RFI and EMI
- · Reduced snubbing

#### **DESCRIPTION**

HEXFRED® diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. An extensive characterization of the recovery behavior for different values of current, temperature and dl/dt simplifies the calculations of losses in the operating conditions. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for power converters, motors drives and other applications where switching losses are significant portion of the total losses.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Cathode to anode voltage	V <sub>R</sub>		400	V
Continuous forward current	I <sub>F</sub>	T <sub>C</sub> = 25 °C	395	
Continuous forward current		T <sub>C</sub> = 100 °C	200	А
Single pulse forward current	I <sub>FSM</sub>	Limited by junction temperature	1200	
Non-repetitive avalanche energy	E <sub>AS</sub>	$L = 100 \mu H$ , duty cycle limited by maximum $T_J$	1.4	mJ
Maying mayor dissination	P <sub>D</sub>	T <sub>C</sub> = 25 °C	657	10/
Maximum power dissipation		T <sub>C</sub> = 100 °C	263	W
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 55 to + 150	°C

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V <sub>BR</sub>	I <sub>R</sub> = 100 μA		400	-	-	
Maximum forward voltage	V <sub>FM</sub>	I <sub>F</sub> = 180 A	See fig. 1	=	1.08	1.46	V
		I <sub>F</sub> = 360 A		=	1.22	1.8	
I <sub>F</sub> = 180 A, T <sub>J</sub> = 125 °C			=	0.99	1.34		
Maximum reverse leakage current	I <sub>RM</sub>	$T_{J} = 125  ^{\circ}\text{C},  V_{R} = 400  \text{V}$ See fig. 2		-	-	4	mA
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V See fig. 3		=	370	500	pF
Series inductance	L <sub>S</sub>	From top of terminal hole to mounting plane		-	6.0	-	nH

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# HFA180NH40PbF

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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time See fig. 5		T <sub>J</sub> = 25 °C		-	90	140	no
	ι <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	280	440	ns
Peak recovery current	I IDDM	T <sub>J</sub> = 25 °C		-	9	16	_
See fig. 6		IRRM	T <sub>J</sub> = 125 °C	I <sub>F</sub> = 135 A dI <sub>F</sub> /dt = 200 A/μs	-	18	32
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C	$V_R = 200 \text{ V}$	-	300	950	nC
See fig. 7		T <sub>J</sub> = 125 °C		-	2650	6300	110
Peak rate of recovery current See fig. 8	all /alt	T <sub>J</sub> = 25 °C		-	300	-	Δ /
	dI <sub>(rec)M</sub> /dt	T <sub>J</sub> = 125 °C		-	290	-	A/μs

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction and storage temperature range		T <sub>J</sub> , T <sub>Stg</sub>		- 55 to 150	°C	
Maximum thermal resistance, junction to case		R <sub>thJC</sub>	DC operation See fig. 4	0.19	°C/W	
Typical thermal resistance, case to heatsink		R <sub>thCS</sub>	Mounting surface, smooth and greased	0.05		
Approximate weight				30	g	
Approximate weight				1.06	OZ.	
Manustrantan	minimum			3 (26.5)		
Mounting torque	maximum			4 (35.4)	$N \cdot m$	
Terminal torque -	minimum			3.4 (30)	(lbf · in)	
	maximum			5 (44.2)		
Case style			HALF-PAK module	•		





#### HEXFRED® Ultrafast Soft Recovery Diode, 180 A

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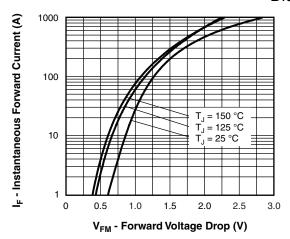


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

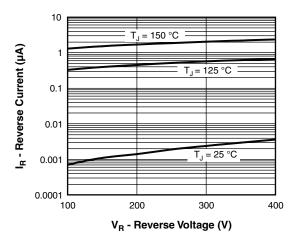


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

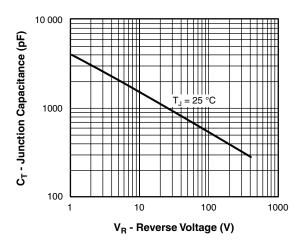


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

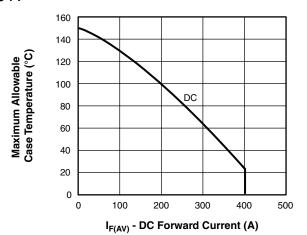


Fig. 4 - Maximum Allowable Case Temperature vs. DC Forward Current

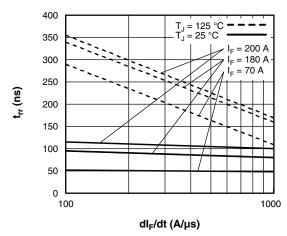


Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

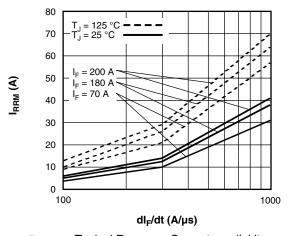


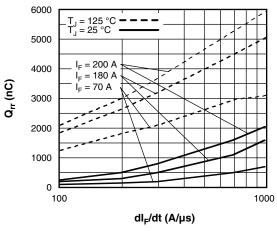
Fig. 6 - - Typical Recovery Current vs. dl<sub>F</sub>/dt

### HFA180NH40PbF

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10 000

200 A
180 A
70 A

T<sub>J</sub> = 125 °C
T<sub>J</sub> = 25 °C

1000

dl<sub>F</sub>/dt (A/µs)

Fig. 7 - - Typical Stored Charge vs. dl<sub>F</sub>/dt

Fig. 8 - Typical  $dl_{(rec)M}/dt$  vs.  $dl_F/dt$ 

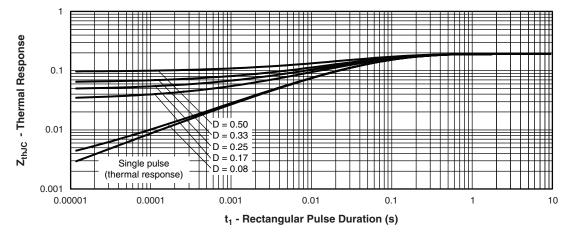


Fig. 9 - Maximum Thermal Impedance  $Z_{\text{thJC}}$  Characteristics



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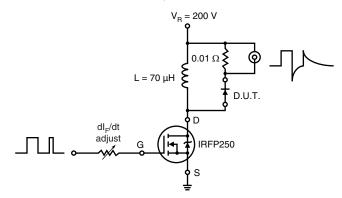
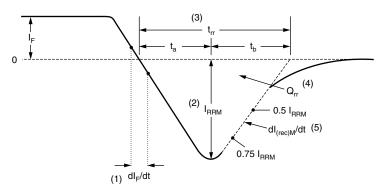


Fig. 10 - Reverse Recovery Parameter Test Circuit



- (1) dI<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_F$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $Q_{rr}$  area under curve defined by  $t_{rr}$  and  $I_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5)  $dI_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

Fig. 11 - Reverse Recovery Waveform and Definitions

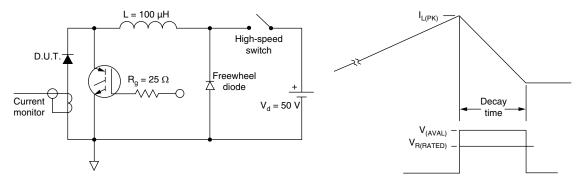


Fig. 12 - Avalanche Test Circuit and Waveforms

# HFA180NH40PbF

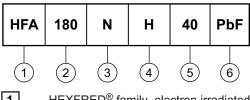
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**HEXFRED® Ultrafast Soft Recovery** Diode, 180 A



#### **ORDERING INFORMATION TABLE**

**Device code** 



- HEXFRED® family, electron irradiated

- Average current rating

- N = Not isolated

- H = HALF-PAK

- Voltage rating (400 V)

- Lead (Pb)-free

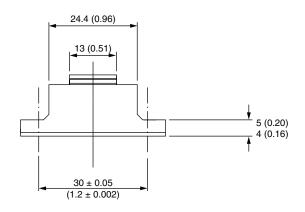
LINKS TO RELATED DOCUMENTS				
Dimensions	http://www.vishay.com/doc?95020			

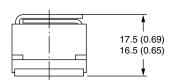


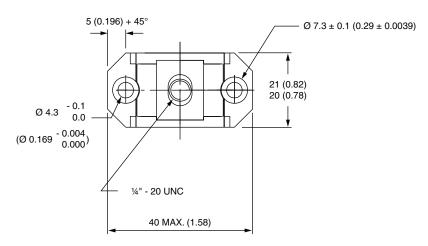
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### **D-67 HALF-PAK**

#### **DIMENSIONS** in millimeters (inches)









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